

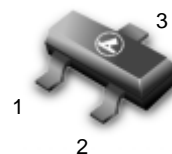
General Purpose Transistors

PNP Silicon

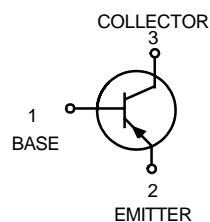
FEATURE

- High current capacity in compact package.
- Epitaxial planar type.
- PNP complement: L8550H
- We declare that the material of product compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

L8550HPLT1G
Series
S-L8550HPLT1G
Series



SOT-23



DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
L8550HPLT1G	s-L8550HPLT1G 1HB	3000/Tape&Reel
L8550HPLT3G	s-L8550HPLT3G 1HB	10000/Tape&Reel
L8550HQLT1G	s-L8550HQLT1G 1HD	3000/Tape&Reel
L8550HQLT3G	s-L8550HQLT3G 1HD	10000/Tape&Reel
L8550HRLT1G	s-L8550HRLT1G 1HF	3000/Tape&Reel
L8550HRLT3G	s-L8550HRLT3G 1HF	10000/Tape&Reel
L8550HSLT1G	s-L8550HSLT1G 1HH	3000/Tape&Reel
L8550HSLT3G	s-L8550HSLT3G 1HH	10000/Tape&Reel

MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V_{CEO}	-25	V
Collector-Base Voltage	V_{CBO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-1500	mA _{dc}

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,(1) $T_A=25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance,Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate,(2) $T_A=25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance,Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_j, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

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ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage (I _C =-1.0mA)	V _{(BR)CEO}	-25	-	-	V
Emitter-Base Breakdown Voltage (I _E =-100μA)	V _{(BR)EBO}	-5	-	-	V
Collector-Base Breakdown Voltage (I _C =-100μA)	V _{(BR)CBO}	-40	-	-	V
Collector Cutoff Current (V _{CB} =-35V)	I _{CBO}	-	-	-150	nA
Emitter Cutoff Current (V _{EB} =-4V)	I _{EBO}	-	-	-150	nA

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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ON CHARACTERISTICS

DC Current Gain I _C =-100mA, V _{CE} =-1V	H _{FE}	100	-	600	
Collector-Emitter Saturation Voltage (I _C =-800mA, I _B =-80mA)	V _{CE(S)}	-	-	-0.5	V

NOTE :

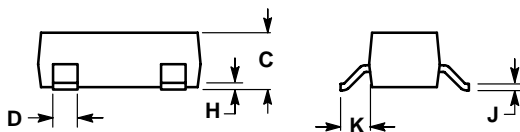
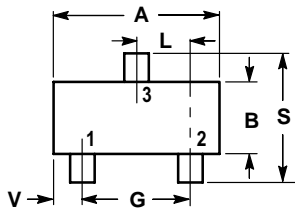
*	P	Q	R	S
h _{FE}	100~200	150~300	200~400	300~600

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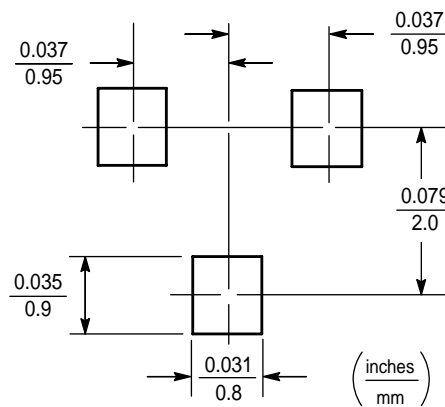
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

- PIN 1. BASE
2. EMITTER
3. COLLECTOR



单击下面可查看定价，库存，交付和生命周期等信息

[>>LRC\(乐山无线电\)](#)